

IN THE CLAIMS

Cancel in this divisional application original claims 1-23 of the prior application U.S. Serial No. 09/970,758.

Amend Claims 24-26 as follows:

Claims 1 –23. Canceled.

Claim 24 (Currently Amended). A power semiconductor device made in accordance with a the method of ~~claim 1~~ comprising the steps of:

A. providing a substrate of a first conductivity type;

B. forming a voltage sustaining region on said substrate by:

1. depositing an epitaxial layer on the substrate, said epitaxial layer having a first conductivity type;

2. forming at least one terraced trench in said epitaxial layer, said terraced trench having a plurality of portions that differ in width to define at least one annular ledge therebetween;

3. depositing a barrier material along the walls and bottom of said trench;

4. implanting a dopant of a second conductivity type through the barrier material lining said at least one annular ledge and said trench bottom and into adjacent portions of the epitaxial layer;

5. diffusing said dopant to form at least one annular doped region in said epitaxial layer and at least one other region located below said annular doped region in said epitaxial layer;

6. depositing a filler material in said terraced trench to substantially fill said terraced trench; and

C. forming over said voltage sustaining region at least one region of said second conductivity type to define a junction therebetween.

Claim 25 (Currently Amended). A power semiconductor device made in accordance with a ~~the method of claim 7~~ comprising the steps of:

A. providing a substrate of a first conductivity type;

B. forming a voltage sustaining region on said substrate by:

1. depositing an epitaxial layer on the substrate, said epitaxial layer having a first conductivity type;

3. forming at least one terraced trench in said epitaxial layer, said terraced trench having a plurality of portions that differ in width to define at least one annular ledge therebetween;

3. depositing a barrier material along the walls and bottom of said trench;

4. implanting a dopant of a second conductivity type through the barrier material lining said at least one annular ledge and said trench bottom and into adjacent portions of the epitaxial layer;

5. diffusing said dopant to form at least one annular doped region in said epitaxial layer and at least one other region located below said annular doped region in said epitaxial layer;

7. depositing a filler material in said terraced trench to substantially fill said terraced trench; and

C. forming over said voltage sustaining region at least one region of said second conductivity type to define a junction therebetween,

wherein said plurality of portions of the terraced trench are coaxially located with respect to one another, and

wherein said plurality of portions of the terraced trench includes at least three portions that differ in width from one another to define at least two annular ledges and said at least one annular doped region includes at least two annular doped regions, and

wherein the step of forming at least one terraced trench includes the steps of successively etching said at least three portions of the terraced trench beginning with a largest width portion and ending with a smallest width portion.

Claim 26 (Currently Amended). A power semiconductor device made in accordance with a ~~the method of claim 9~~ comprising the steps of:

A. providing a substrate of a first conductivity type;

B. forming a voltage sustaining region on said substrate by:

1. depositing an epitaxial layer on the substrate, said epitaxial layer having a first conductivity type;

2. forming at least one terraced trench in said epitaxial layer, said terraced trench having a plurality of portions that differ in width to define at least one annular ledge therebetween;

3. depositing a barrier material along the walls and bottom of said trench;

4. implanting a dopant of a second conductivity type through the barrier material lining said at least one annular ledge and said trench bottom and into adjacent portions of the epitaxial layer;

5. diffusing said dopant to form at least one annular doped region in said epitaxial layer and at least one other region located below said annular doped region in said epitaxial layer;

6. depositing a filler material in said terraced trench to substantially fill said terraced trench; and

C. forming over said voltage sustaining region at least one region of said second conductivity type to define a junction therebetween,

wherein step (C) further includes the steps of:

forming a gate conductor above a gate dielectric region;

forming first and second body regions in the epitaxial layer to define a drift region therebetween, said body regions having a second conductivity type;

forming first and second source regions of the first conductivity type in the first and second body regions, respectively.

Claim 27 (Original). A power semiconductor device comprising:

- a substrate of a first conductivity type;

- a voltage sustaining region disposed on said substrate, said voltage sustaining region including:

 - an epitaxial layer having a first conductivity type;

 - at least one terraced trench located in said epitaxial layer, said terraced trench having a plurality of portions that differ in width to define at least one annular ledge therebetween;

 - at least one annular doped region having a dopant of a second conductivity type, said annular doped region being located in said epitaxial layer below and adjacent to said annular ledge;

 - a filler material substantially filling said terraced trench; and

 - at least one active region of said second conductivity disposed over said voltage sustaining region to define a junction therebetween.

Claim 28 (Original). The device of claim 27 wherein said plurality of portions of the terraced trench includes a smallest width portion and a largest width portion, said smallest width portion being located at a depth in said epitaxial layer such that it is closer to the substrate than a largest width portion.

Claim 29 (Original). The device of claim 28 wherein said plurality of portions of the terraced trench are coaxially located with respect to one another.

Claim 30 (Original). The device of claim 27 wherein said plurality of portions of the terraced trench includes at least three portions that differ in width from one another to define at least two annular ledges and said at least one annular doped region includes at least two annular doped regions.

Claim 31 (Original). The device of claim 29 wherein said plurality of portions of the terraced trench includes at least three portions that differ in width from one another to define at least two annular ledges and said at least one annular doped region includes at least two annular doped regions.

Claim 32 (Original). The device of claim 27 wherein said epitaxial layer has a given thickness and further comprising the step of etching a first portion of the terraced trench by an amount substantially equal to $1/(x+1)$ of said given thickness, where x is equal to or greater than a prescribed number of annular doped regions to be formed in the voltage sustaining region.

Claim 33 (Original). The device of claim 27 wherein said material filling the trench is a dielectric material.

Claim 34 (Original). The device of claim 33 wherein said dielectric material is silicon dioxide.

Claim 35 (Original). The device of claim 34 wherein said dielectric material is silicon nitride.

Claim 36 (Original). The device of claim 27 wherein said dopant is boron.

Claim 37 (Original). The device of claim 31 wherein a surface area of the at least two annular ledges are substantially equal to one another.

Claim 38 (Original). The device of claim 27 wherein said at least one active region further includes:

- a gate dielectric and a gate conductor disposed above said gate dielectric;
- first and second body regions located in the epitaxial layer to define a drift region therebetween, said body regions having a second conductivity type; and
- first and second source regions of the first conductivity type located in the first and second body regions, respectively.

Claim 39 (Original). The device of claim 38 wherein said body regions include deep body regions.

Claim 40 (Original). The device of claim 27 wherein said terraced trench has a circular cross-section.

Claim 41 (Original). The device of claim 27 wherein said terraced trench has a cross-sectional shape selected from the group consisting of a square, rectangle, octagon, and a hexagon.